

SPECIFICATION

Device Name : Intelligent Power MOSFET

Type Name : F5033

Spec. No. : **MS5F4292**

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Fuji Electric Co., Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.	
DRAWN	April-2-1978	<i>S. Suzuki</i>		DWG. NO.	MS5F4292 1/12
CHECKED	April 2/78	<i>S. Suzuki</i>	<i>S. Suzuki</i>		

1. Scope
This specifies Fuji Intelligent Power MOSFET F5033
2. Construction
Self-Isolation Structure
Output Part: N-channel enhancement mode power MOSFET
3. Application
For switching
4. Outview
SOP-8(EIAJ SC-87) Outview See to 6/12 page)
5. Absolute maximum ratings (at $T_j=25^\circ\text{C}$, unless otherwise specified.)

Description	Symbol	Characteristics	Unit	Conditions
Drain-source voltage	V_{DS}	4.0	V	DC
Gate-source voltage	V_{GS}	DC-0.3~7.0	V	DC
Continuous drain current	I_D	1	A	————
Maximum power dissipation	P_D	1.5	W	†
Operating junction temperature	T_j	150	$^\circ\text{C}$	————
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$	————

† Surface Mounted on 1000mm²PCB(FR-4)

6. Electrical characteristics (at $T_j=25^\circ\text{C}$, unless otherwise specified.)

Description	Symbol	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Drain-source clamp voltage	V_{DS}	$I_D = 1\text{mA}$ $V_{GS} = 0\text{V}$	4.0		6.0	V
Gate threshold voltage	$V_{GS(th)}$	$I_D = 10\text{mA}$ $V_{DS} = 1.3\text{V}$	1.0		2.8	V
Operation gate voltage	$V_{GS(op)}$		3.5		7.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 3.0\text{V}$ $V_{GS} = 0\text{V}$			1.0	mA
Gate-source leakage current	$I_{GS(n)}$	* $V_{GS} = 5\text{V}$			500	μA
	$I_{GS(un)}$		**		800	μA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 0.5\text{A}$ $V_{GS} = 5\text{V}$			600	m Ω

* Under normal operation ** Under self protection

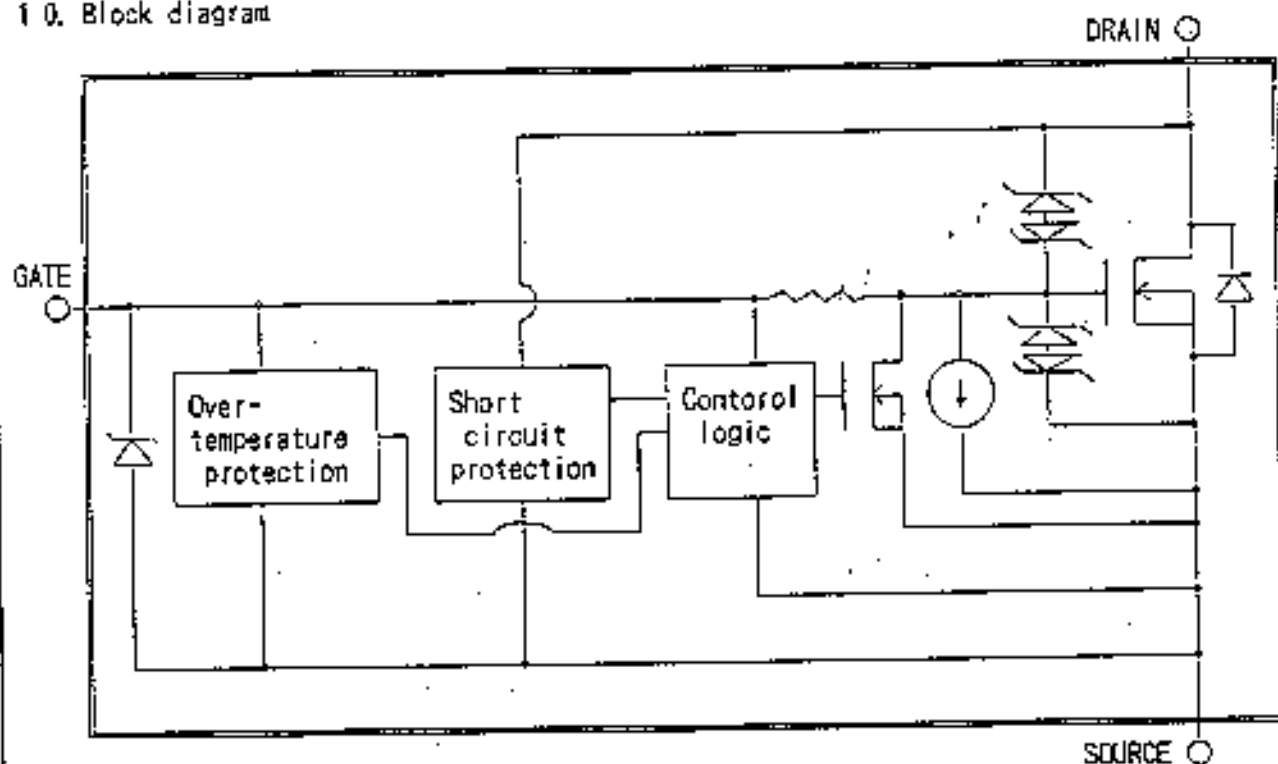
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1 0. Block diagram



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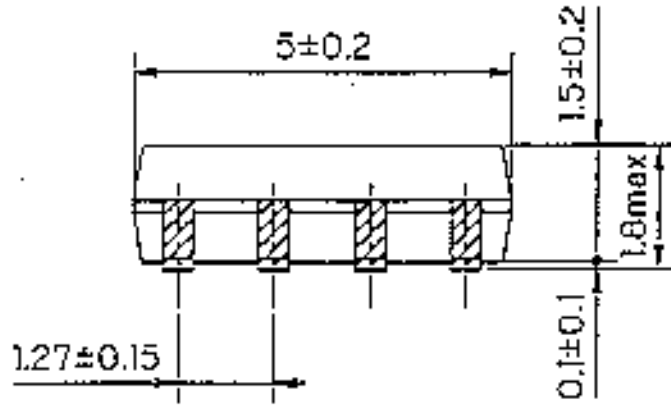
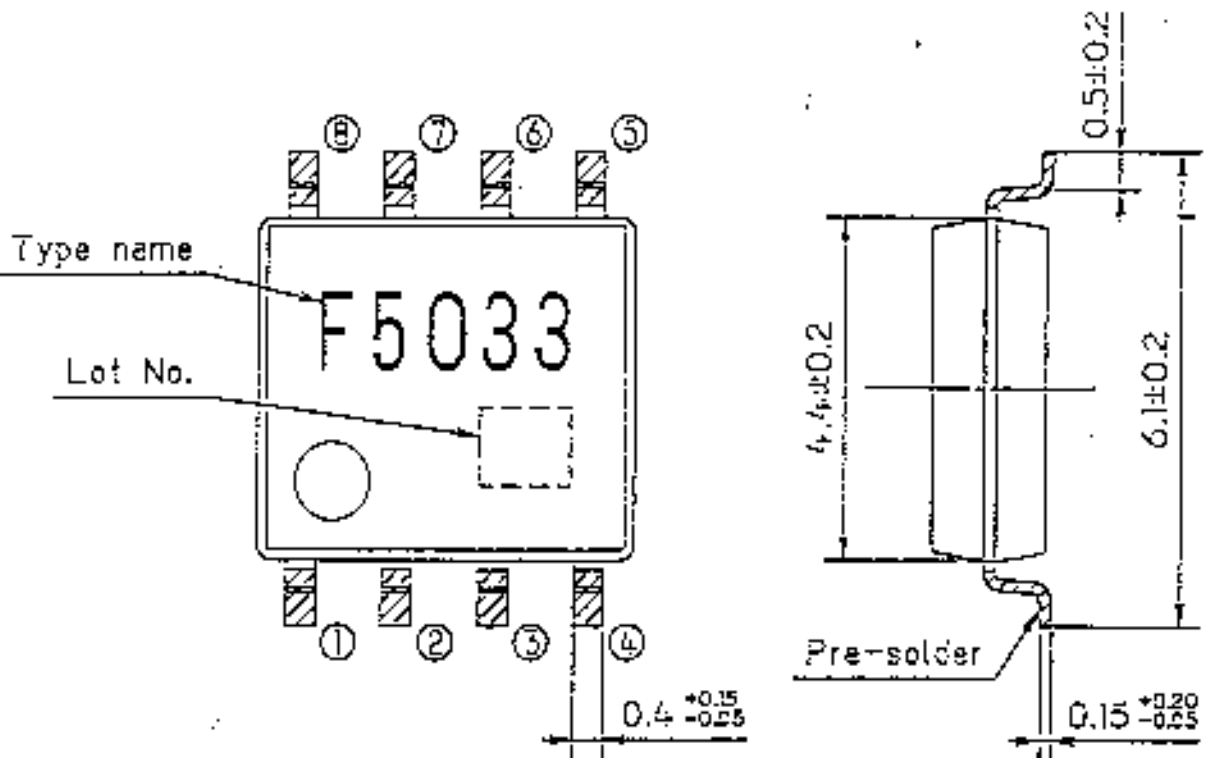
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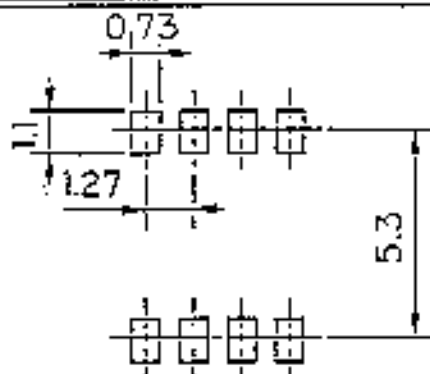
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FUJI INTELLIGENT POWER MOS FET

TYPE : F5033



RECOMMENDED PATTERN OF SOLDERING PADS.



CONNECTION

- ① SOURCE 1
- ② GATE 1
- ③ SOURCE 2
- ④ GATE 2
- ⑤ ⑥ DRAIN 2.
- ⑦ ⑧ DRAIN 1

EIAJ : SC-87

DIMENSIONS ARE IN MILLIMETERS.

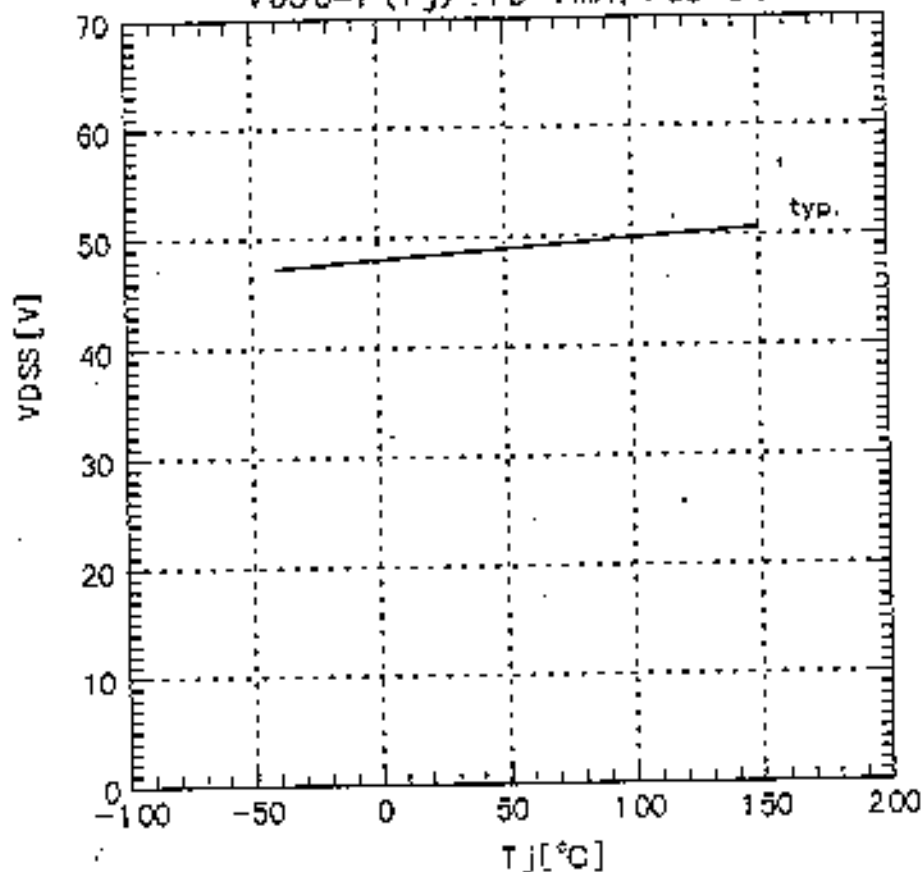
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1	1
2	1
3	1
4	1
5	1
6	1
7	1
8	1

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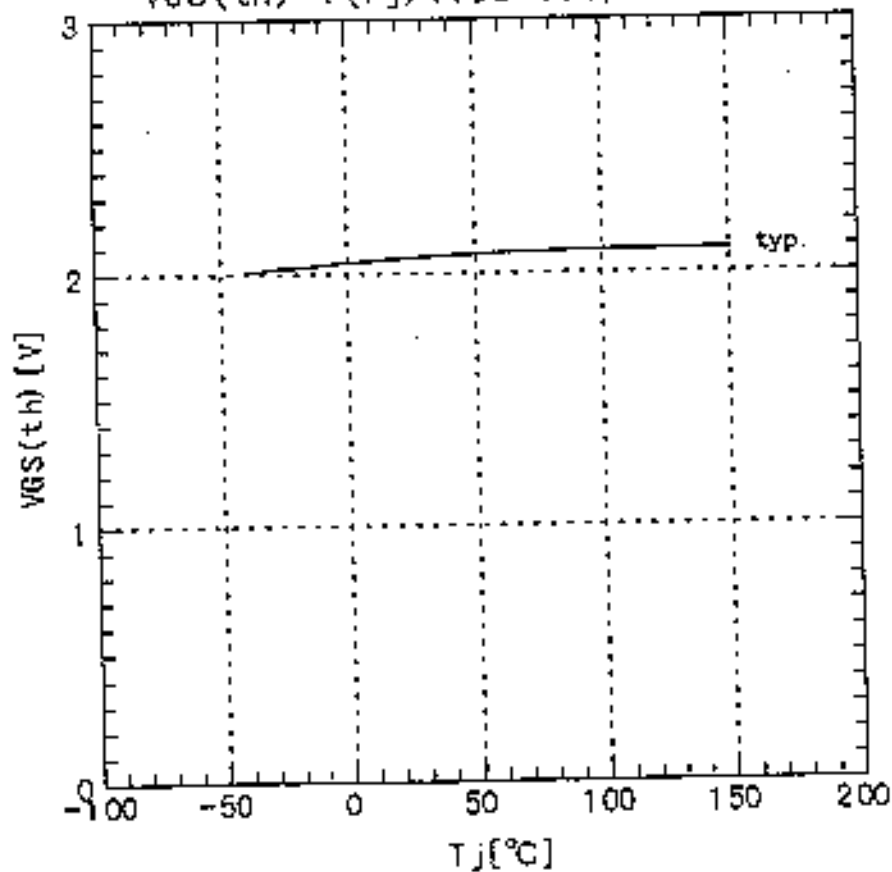
Drain-source clamp voltage

$V_{DSS} = f(T_j) : I_D = 1\text{mA}, V_{GS} = 0\text{V}$



Gate threshold voltage

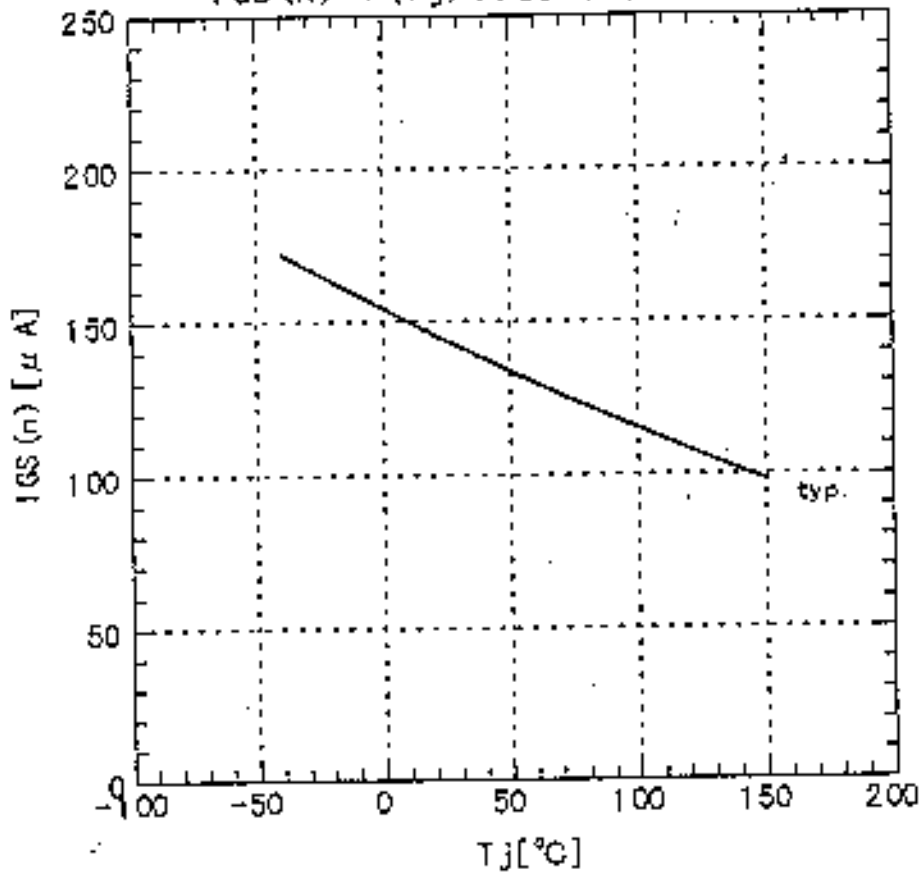
$V_{GS(th)} = f(T_j) : V_{DS} = 13\text{V}, I_D = 10\text{mA}$



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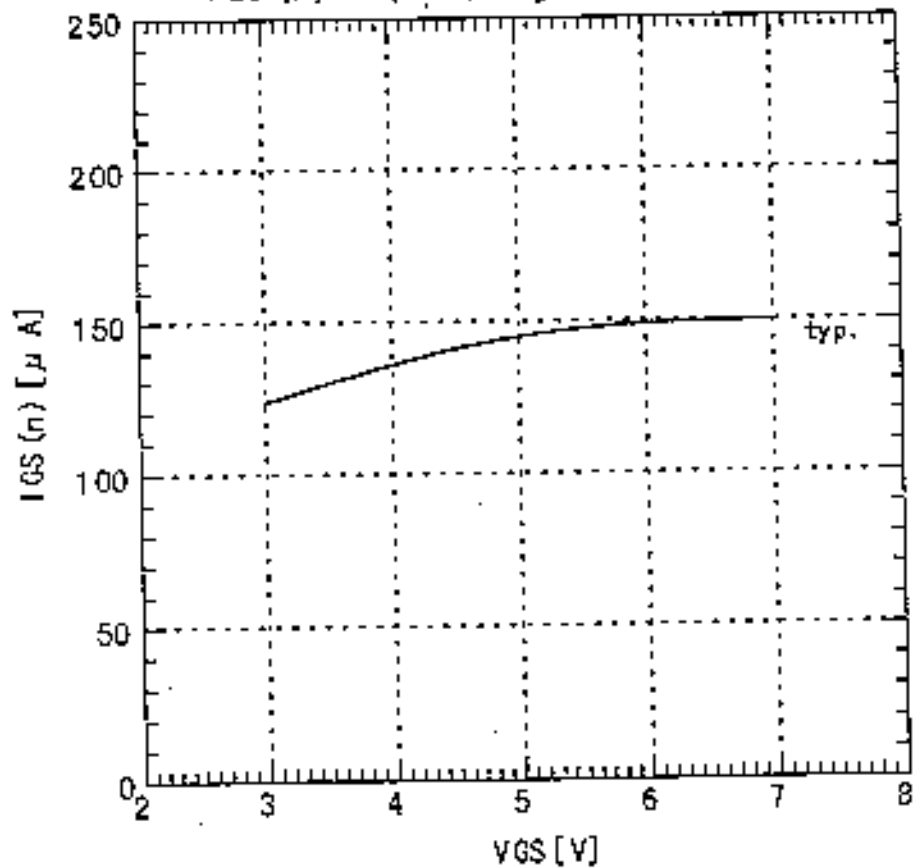
Gate-source leakage current

$$I_{GS}(\mu A) = f(T_j) : V_{GS} = 5V, V_{DS} = 0V$$

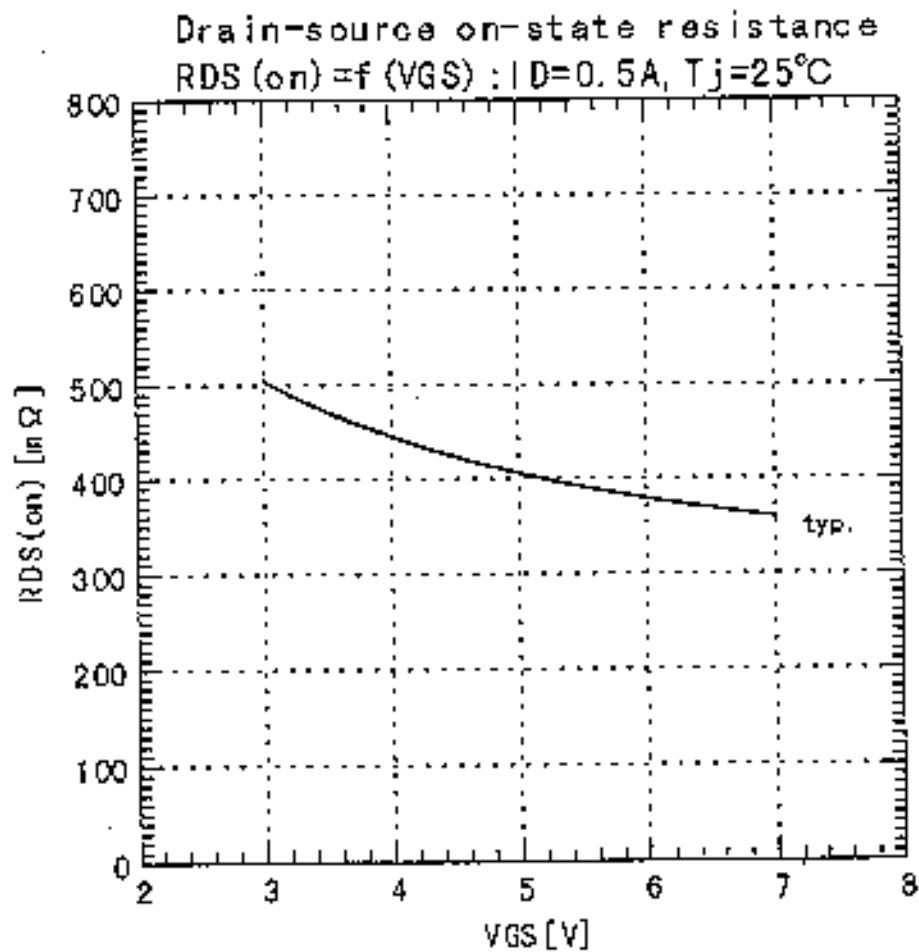
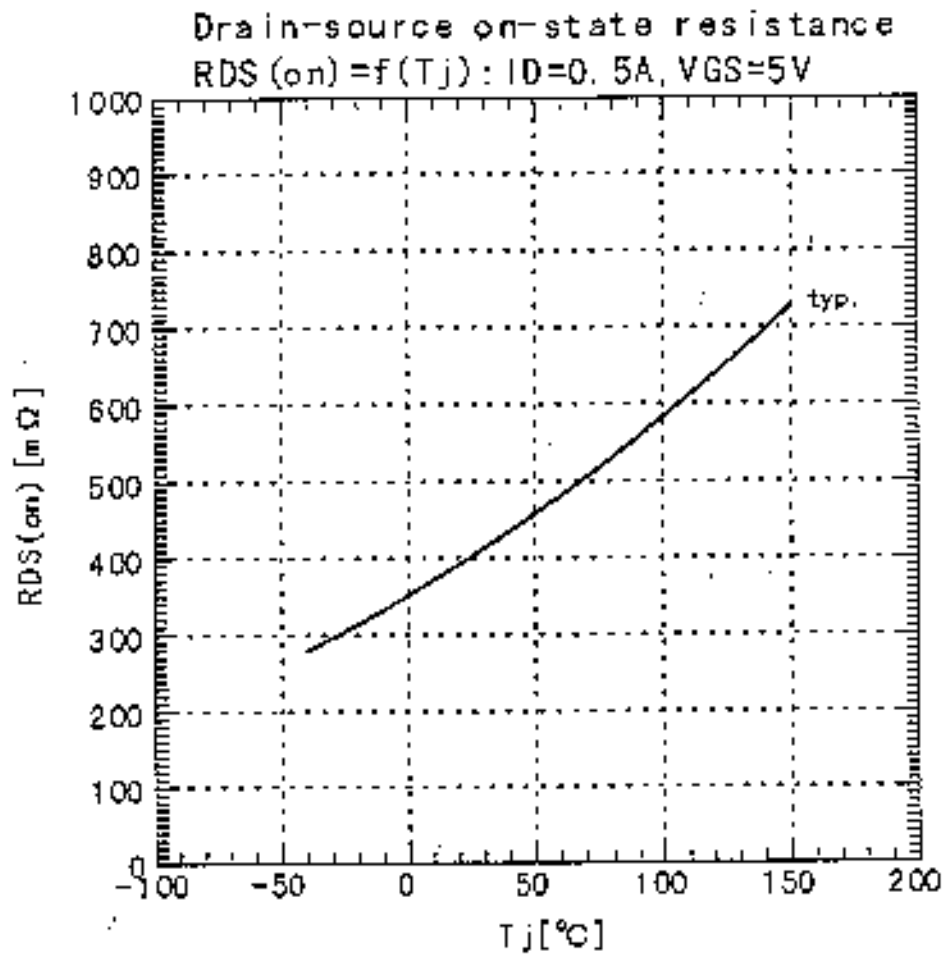


Gate-source leakage current

$$I_{GS}(\mu A) = f(V_{GS}) : T_j = 25^{\circ}C, V_{DS} = 0V$$



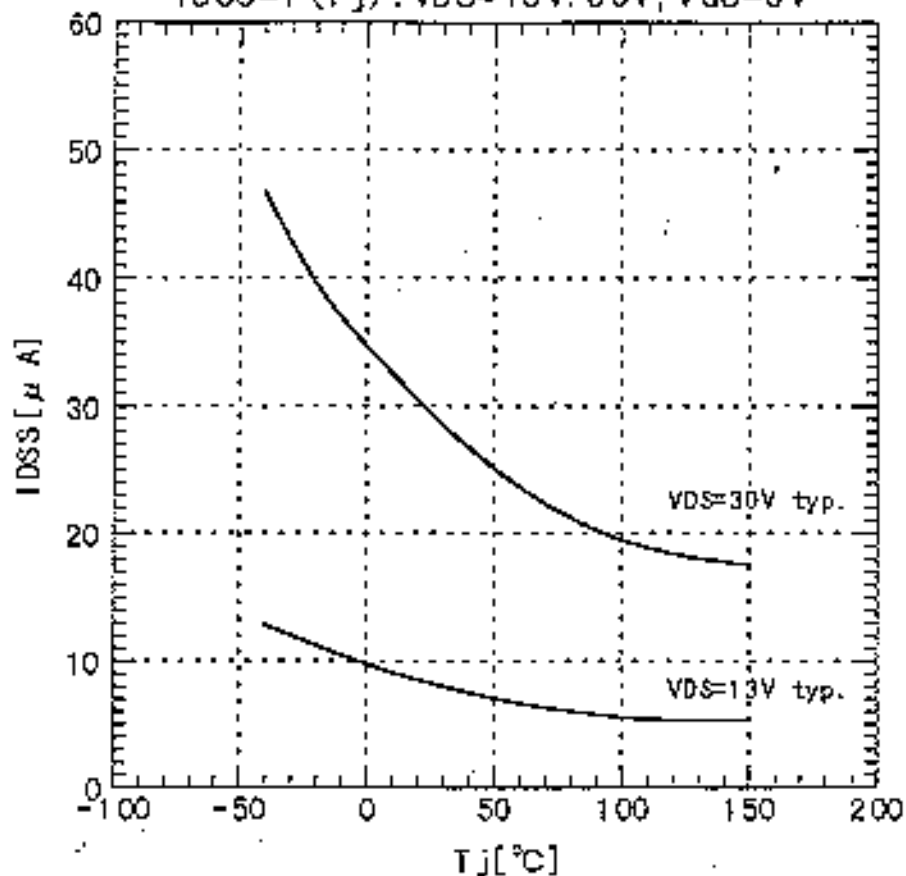
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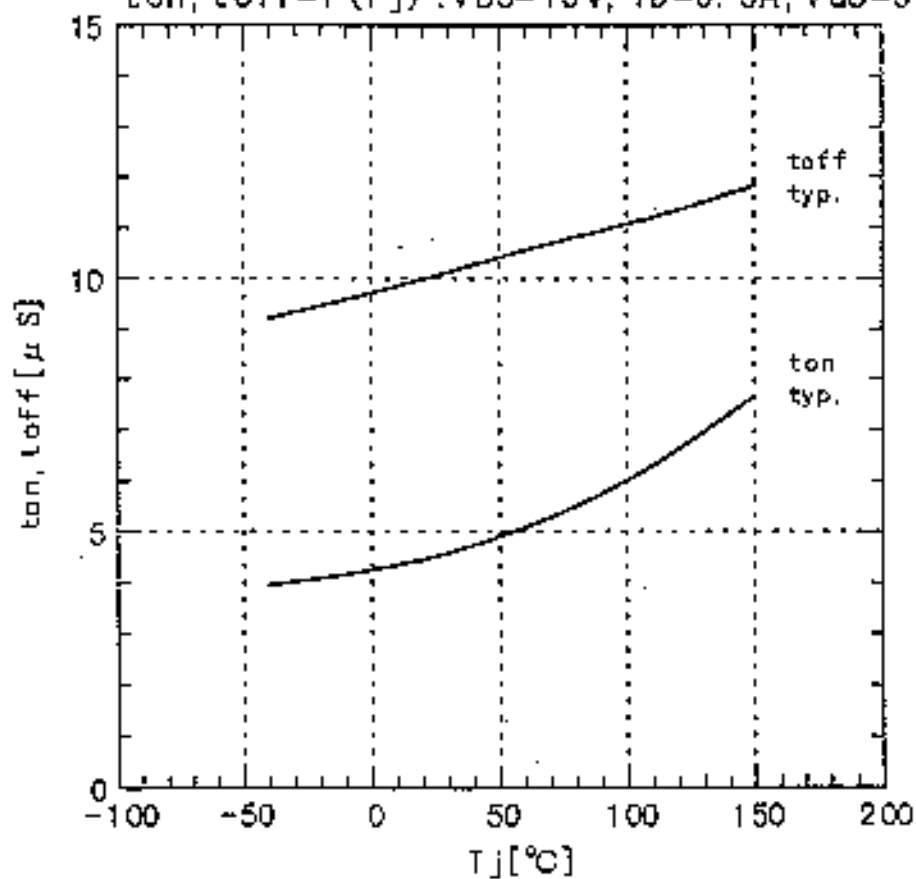
Zero gate voltage drain current

$$I_{DSS} = f(T_j) : V_{DS} = 13V, 30V, V_{GS} = 0V$$



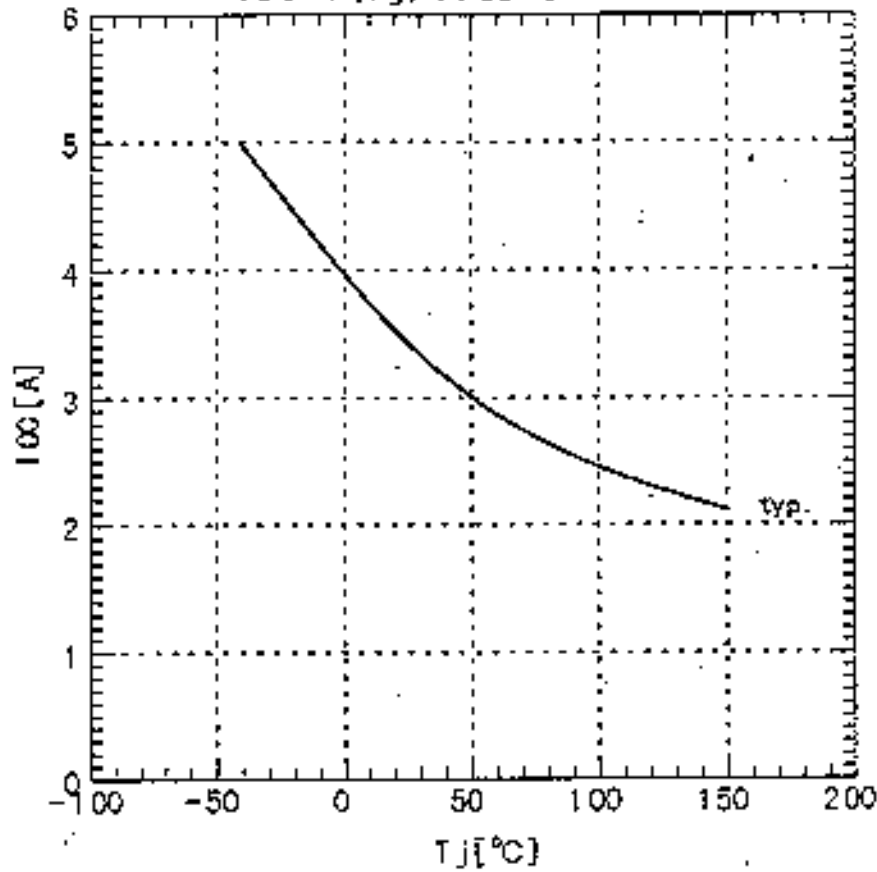
Turn-on time, Turn-off time

$$t_{on}, t_{off} = f(T_j) : V_{DS} = 13V, I_D = 0.5A, V_{GS} = 5V$$

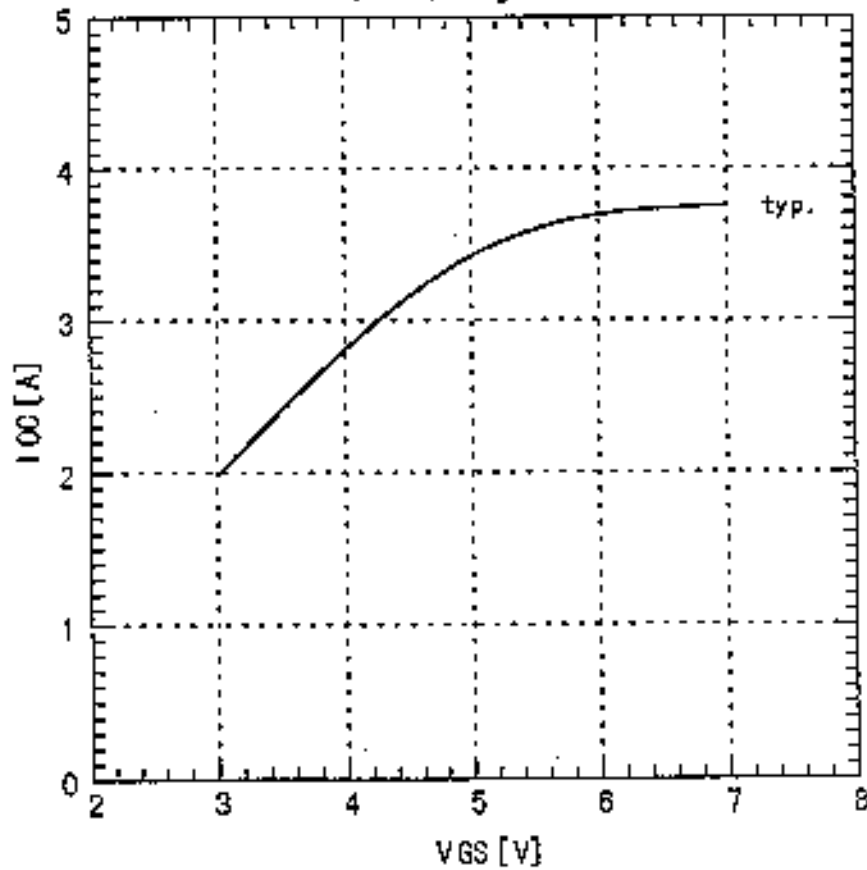


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Short circuit protection
 $I_{OC}=f(T_j) : V_{GS}=5V$

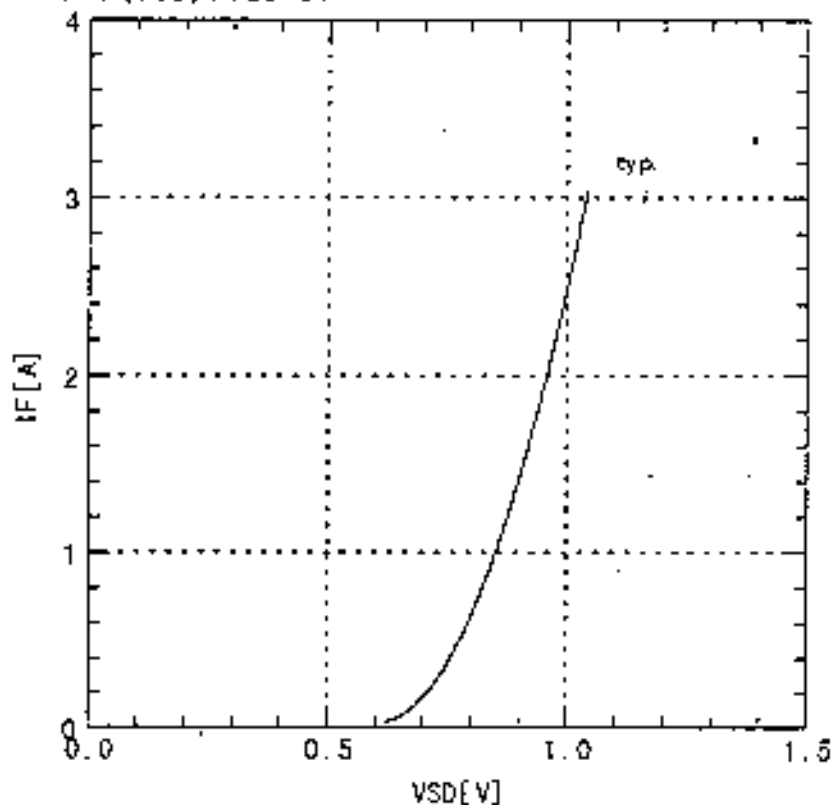


Short circuit protection
 $I_{OC}=f(V_{GS}) : T_j=25^\circ C$



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Forward characteristic of reverse of diode
 $I_F = f(V_{SD}) : V_{GS} = 0V$



Continuous drain current VS Ambient temperature
 $I_D = f(T_a) : \text{Mounting Pad Size } (\beta) = 5\text{mm}$

